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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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Inverter Grade Thyristors (Stud Version), 175 A



TO-209AB (TO-93)

FEATURES

- All diffused design
- Center amplifying gate
- Guaranteed high dV/dt
- Guaranteed high dI/dt
- High surge current capability
- Low thermal impedance
- High speed performance
- Compression bonding
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912


**RoHS
COMPLIANT**
PRODUCT SUMMARY

$I_{T(AV)}$	175 A
V_{DRM}/V_{RRM}	1000 V, 1200 V
V_{TM}	2.07 V
I_{TSM} at 50 Hz	4680 A
I_{TSM} at 60 Hz	4900 A
I_{GT}	200 mA
T_J	-40 °C to 125 °C
Package	TO-209AB (TO-93)
Diode variation	Single SCR

TYPICAL APPLICATIONS

- Inverters
- Choppers
- Induction heating
- All types of force-commutated converters

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		175	A
	T_C	85	°C
$I_{T(RMS)}$		275	
I_{TSM}	50 Hz	4680	A
	60 Hz	4900	
I^2t	50 Hz	110	kA ² s
	60 Hz	100	
V_{DRM}/V_{RRM}		1000 to 1200	V
t_q	Range	15 to 25	μs
T_J		-40 to 125	°C

ELECTRICAL SPECIFICATIONS
VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-ST173S	10	1000	1100	40
	12	1200	1300	



CURRENT CARRYING CAPABILITY							
FREQUENCY							UNITS
50 Hz	500	320	790	550	4510	3310	A
400 Hz	450	290	810	540	1970	1350	
1000 Hz	330	190	760	490	1050	680	
2500 Hz	170	80	510	300	480	280	
Recovery voltage V_r	50		50		50		V
Voltage before turn-on V_d	V_{DRM}		V_{DRM}		V_{DRM}		
Rise of on-state current di/dt	50		-		-		A/μs
Case temperature	60	85	60	85	60	85	°C
Equivalent values for RC circuit	47/0.22		47/0.22		47/0.22		Ω/μF

ON-STATE CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction, half sine wave			175	A
					85	°C
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 75 °C case temperature			275	
Maximum peak, one half cycle, non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reappplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	4680	A
					t = 8.3 ms	
		t = 10 ms	100 % V_{RRM} reappplied		3940	
					t = 8.3 ms	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reappplied		110	kA ² s
					t = 8.3 ms	
		t = 10 ms	100 % V_{RRM} reappplied		77	
					t = 8.3 ms	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reappplied			1100	kA ² √s
Maximum peak on-state voltage	V_{TM}	$I_{TM} = 600$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sine wave pulse			2.07	V
Low level value of threshold voltage	$V_{T(TO)1}$	$(16.7\% \times \pi \times I_{T(AV)}) < I < \pi \times I_{T(AV)}$, $T_J = T_J$ maximum			1.55	
High level value of threshold voltage	$V_{T(TO)2}$	$I > \pi \times I_{T(AV)}$, $T_J = T_J$ maximum			1.58	
Low level value of forward slope resistance	r_{t1}	$(16.7\% \times \pi \times I_{T(AV)}) < I < \pi \times I_{T(AV)}$, $T_J = T_J$ maximum			0.87	
High level value of forward slope resistance	r_{t2}	$I > \pi \times I_{T(AV)}$, $T_J = T_J$ maximum			0.82	mΩ
Maximum holding current	I_H	$T_J = 25$ °C, $I_T > 30$ A			600	mA
Typical latching current	I_L	$T_J = 25$ °C, $V_A = 12$ V, $R_a = 6$ Ω, $I_G = 1$ A			1000	

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum non-repetitive rate of rise of turned on current	di/dt	$T_J = T_J$ maximum, $V_{DRM} = \text{Rated } V_{DRM}$ $I_{TM} = 2 \times di/dt$			1000	A/μs
Typical delay time	t_d	$T_J = 25$ °C, $V_{DM} = \text{Rated } V_{DRM}$, $I_{TM} = 50$ A DC, $t_p = 1$ μs Resistive load, gate pulse: 10 V, 5 Ω source			1.1	μs
Maximum turn-off time	minimum	t_q	$T_J = T_J$ maximum, $I_{TM} = 300$ A, commutating $di/dt = 20$ A/μs $V_R = 50$ V, $t_p = 500$ μs, dV/dt : See table in device code	15		
	maximum			25		



BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum, linear to 80 % V _{DRM} , higher value available on request	500	V/μs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	T _J = T _J maximum, rated V _{DRM} /V _{RRM} applied	40	mA

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}	T _J = T _J maximum, f = 50 Hz, d% = 50	60	W
Maximum average gate power	P _{G(AV)}		10	
Maximum peak positive gate current	I _{GM}	T _J = T _J maximum, t _p ≤ 5 ms	10	A
Maximum peak positive gate voltage	+ V _{GM}		20	
Maximum peak negative gate voltage	- V _{GM}		5	
Maximum DC gate current required to trigger	I _{GT}	T _J = 25 °C, V _A = 12 V, R _a = 6 Ω	200	mA
Maximum DC gate voltage required to trigger	V _{GT}		3	V
Maximum DC gate current not to trigger	I _{GD}	T _J = T _J maximum, rated V _{DRM} applied	20	mA
Maximum DC gate voltage not to trigger	V _{GD}		0.25	V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating temperature range	T _J		-40 to 125	°C
Maximum storage temperature range	T _{Stg}		-40 to 150	
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.105	K/W
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.04	
Mounting torque, ± 10 %		Non-lubricated threads	31 (275)	N · m (lbf · in)
		Lubricated threads	24.5 (210)	
Approximate weight			280	g
Case style		See dimensions - link at the end of datasheet	TO-209AB (TO-93)	

ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.016	0.012	T _J = T _J maximum	K/W
120°	0.019	0.020		
90°	0.025	0.027		
60°	0.036	0.037		
30°	0.060	0.060		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

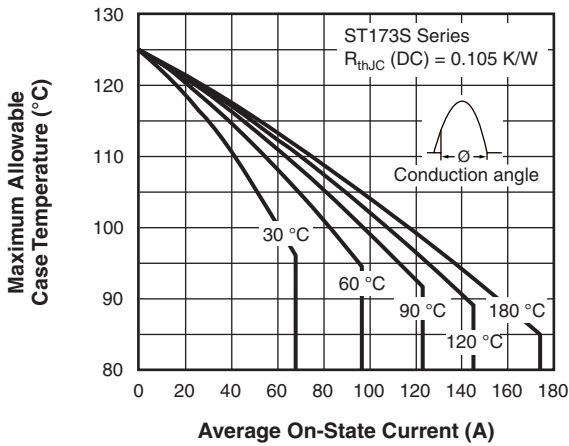


Fig. 1 - Current Ratings Characteristics

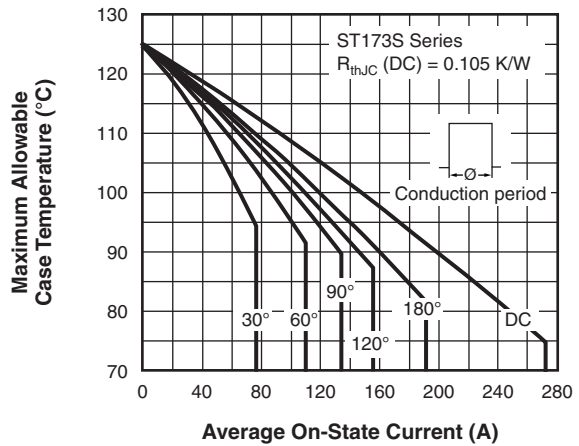


Fig. 2 - Current Ratings Characteristics

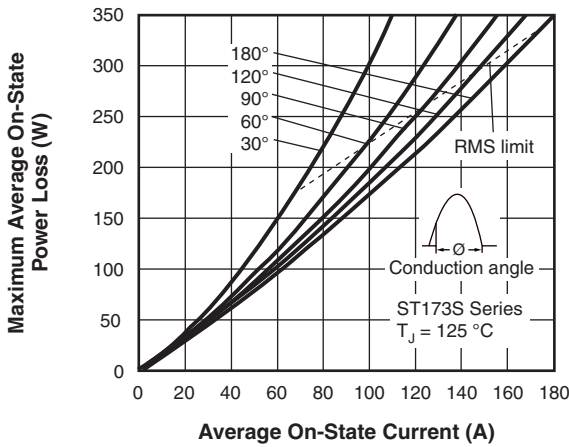


Fig. 3 - On-State Power Loss Characteristics

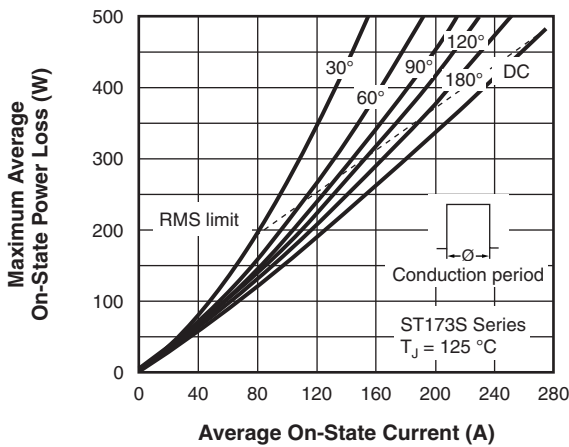
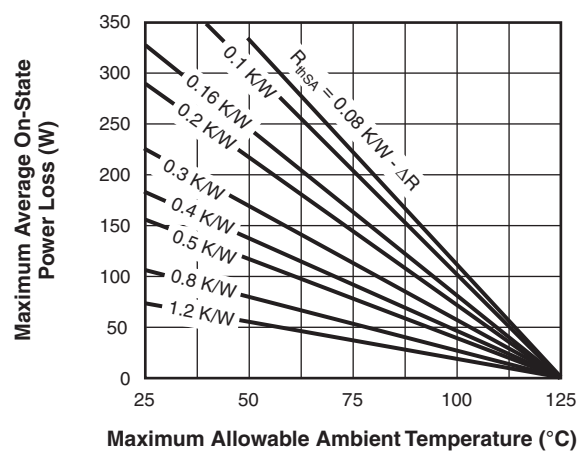
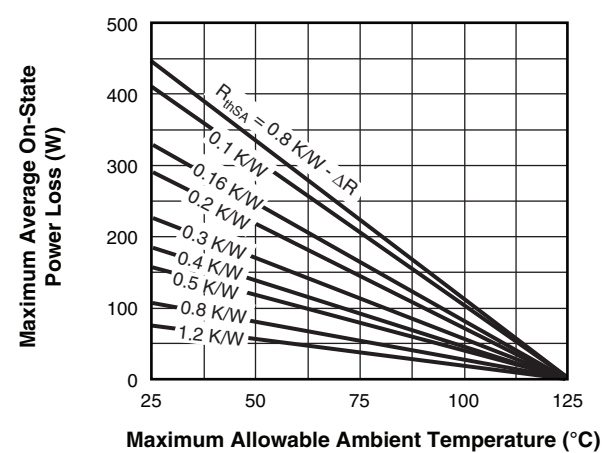


Fig. 4 - On-State Power Loss Characteristics



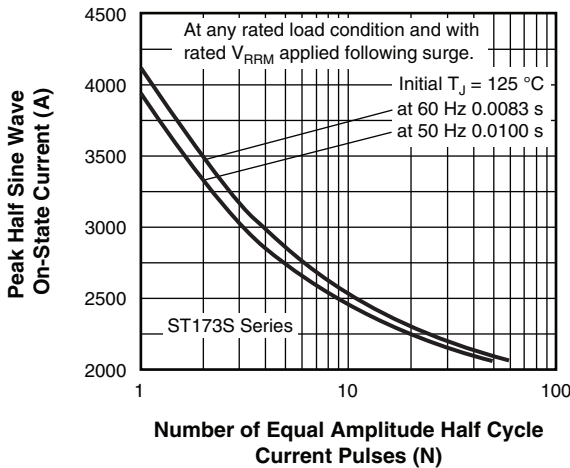


Fig. 5 - Maximum Non-Repetitive Surge Current

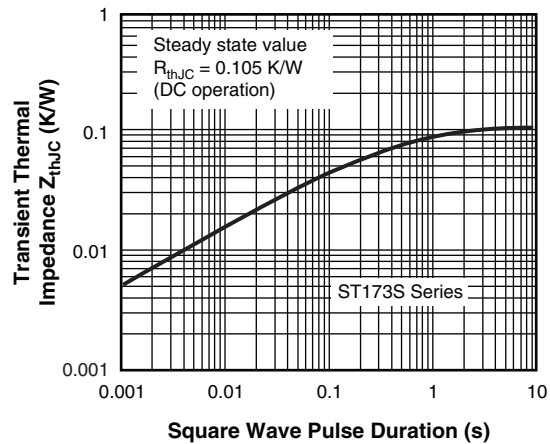


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

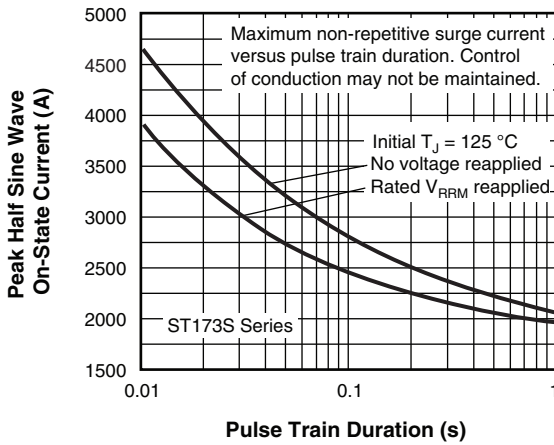


Fig. 6 - Maximum Non-Repetitive Surge Current

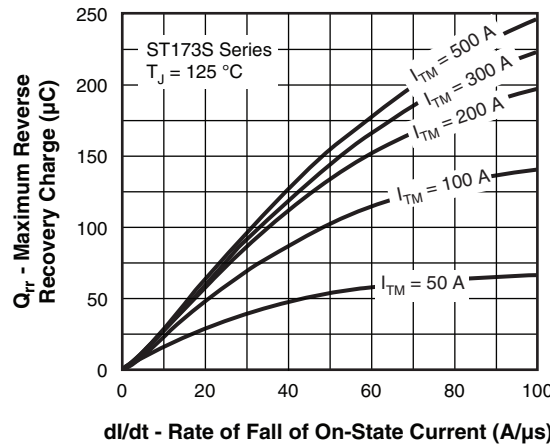


Fig. 9 - Reverse Recovered Current Characteristics

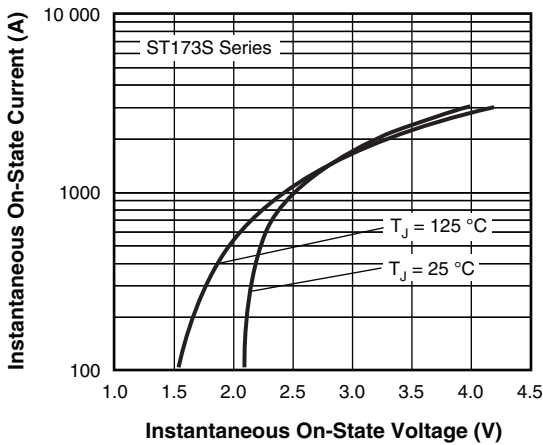


Fig. 7 - On-State Voltage Drop Characteristics

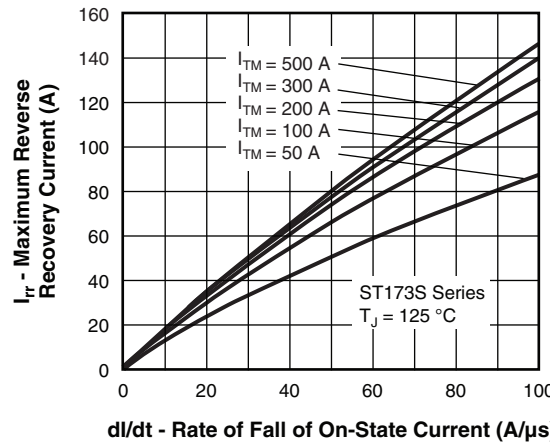


Fig. 10 - Reverse Recovery Current Characteristics

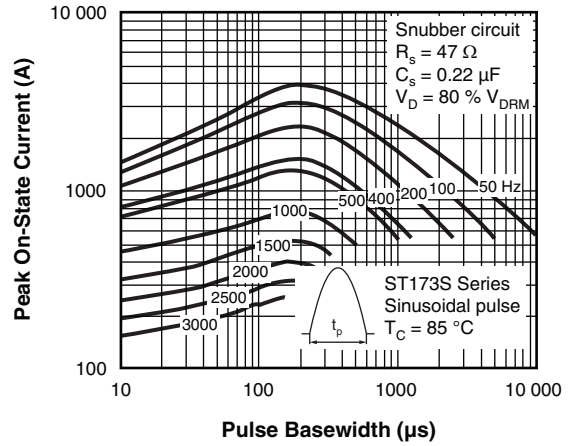
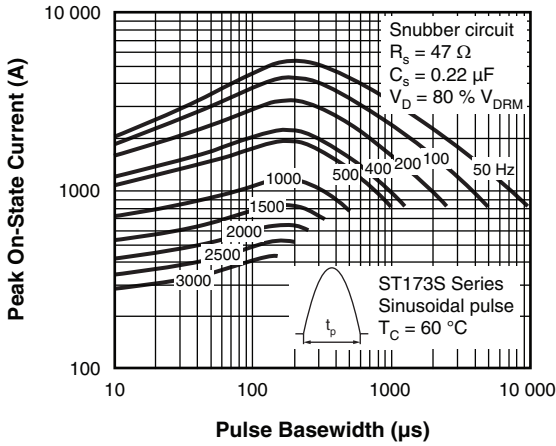


Fig. 11 - Frequency Characteristics

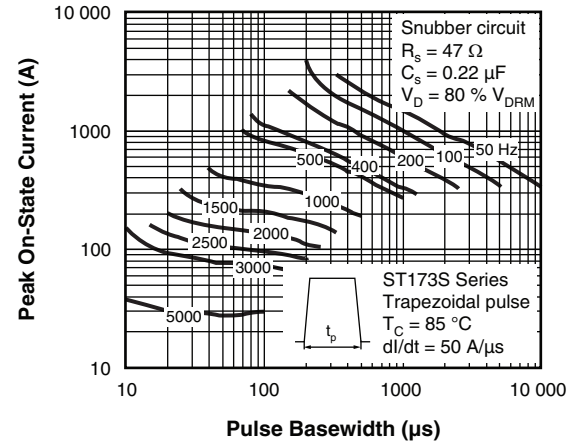
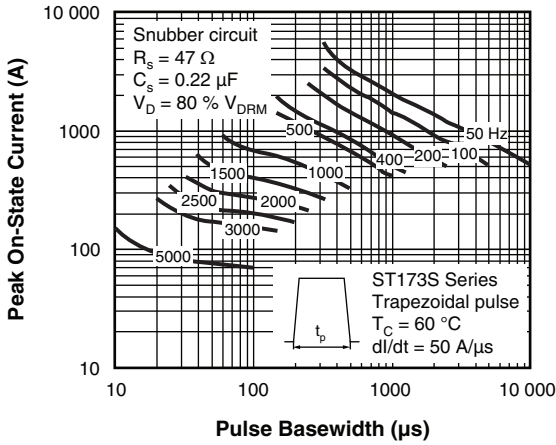


Fig. 12 - Frequency Characteristics

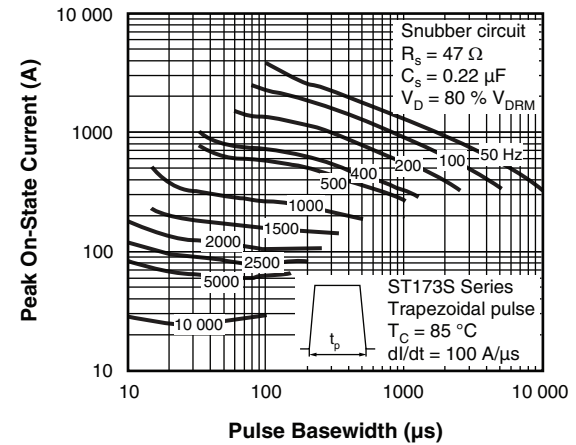
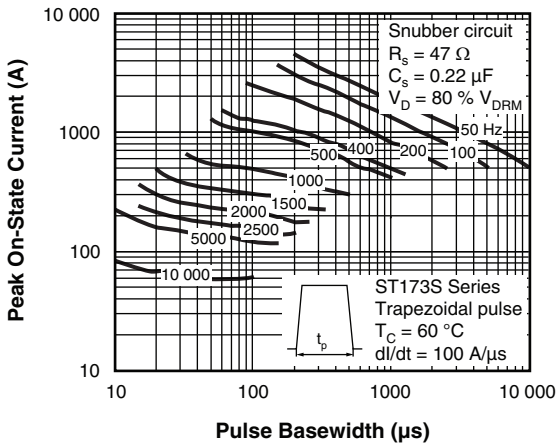


Fig. 13 - Frequency Characteristics

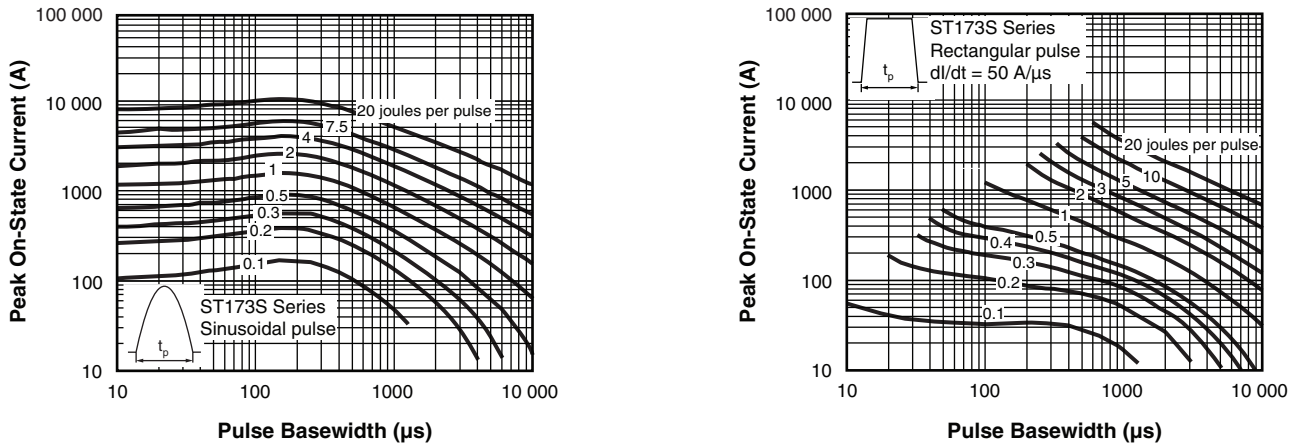


Fig. 14 - Maximum On-State Energy Power Loss Characteristics

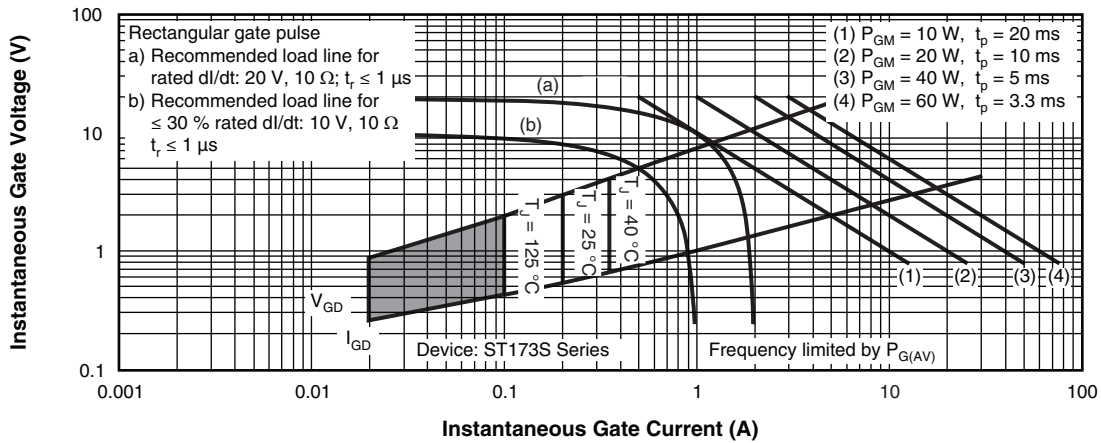
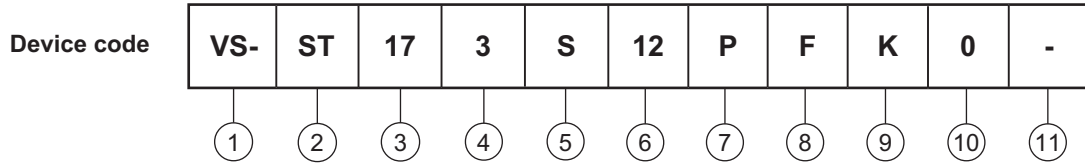


Fig. 15 - Gate Characteristics



ORDERING INFORMATION TABLE



- 1** - Vishay Semiconductors product
- 2** - Thyristor
- 3** - Essential part number
- 4** - 3 = Fast turn-off
- 5** - S = Compression bonding stud
- 6** - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- 7** - P = Stud base 3/4" 16UNF-2A
M = Stud base metric threads M16 x 1.5
- 8** - Reapplied dV/dt code (for t_q test condition)
- 9** - t_q code
- 10** - 0 = Eyelet terminals (gate and aux. cathode leads)
1 = Fast-on terminals (gate and aux. cathode leads)
2 = Flag terminals (for cathode and gate terminals)
- 11** - Critical dV/dt:
 - None = 500 V/ μ s (standard value)
 - L = 1000 V/ μ s (special selection)

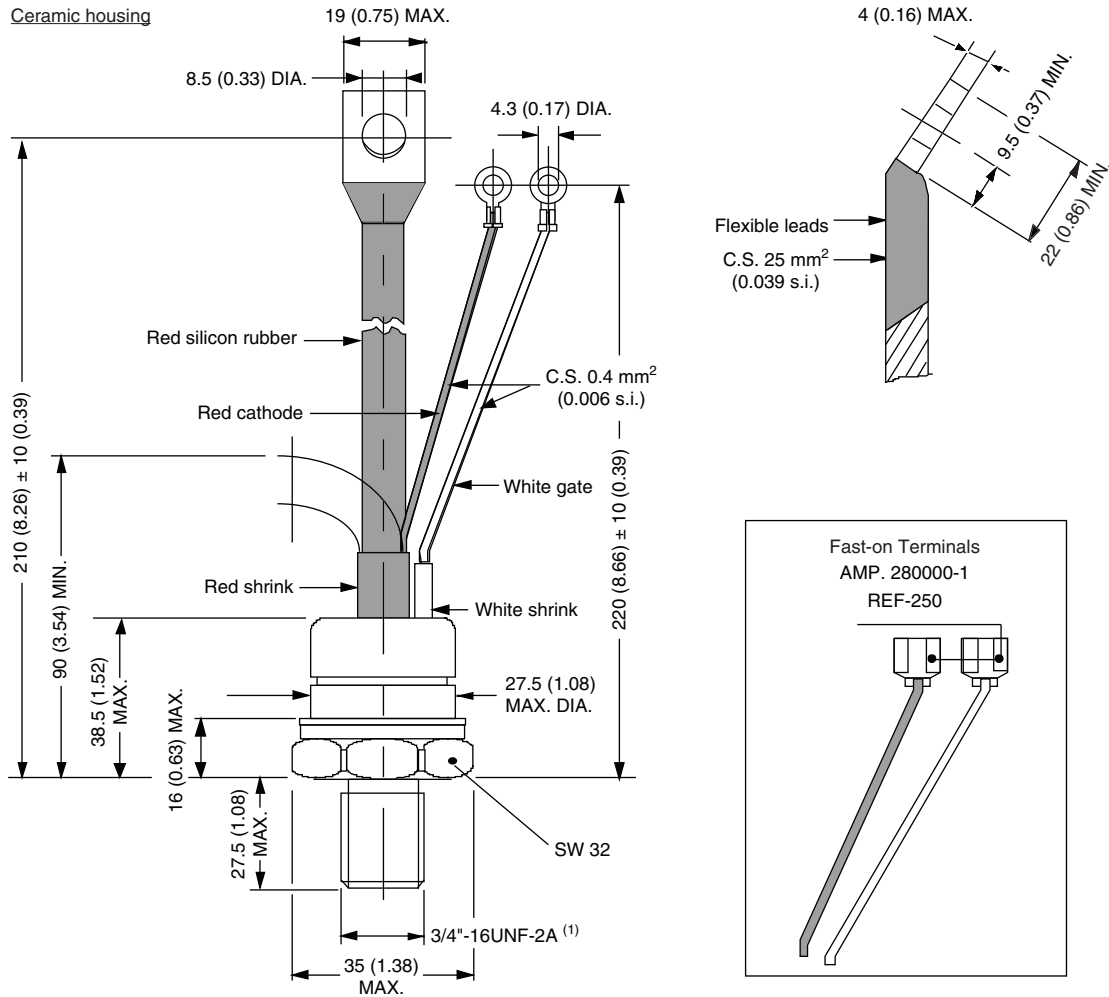
dV/dt - t_q combinations available					
dV/dt (V/ μ s)	20	50	100	200	400
15	CL	-	-	-	-
18	CP	DP	EP	FP*	-
20	CK	DK	EK	FK*	HK
25	CJ	DJ	EJ	FJ	HJ
30	-	DH	EH	FH	HH

* Standard part number.
All other types available only on request.

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95079

TO-209AB (TO-93)

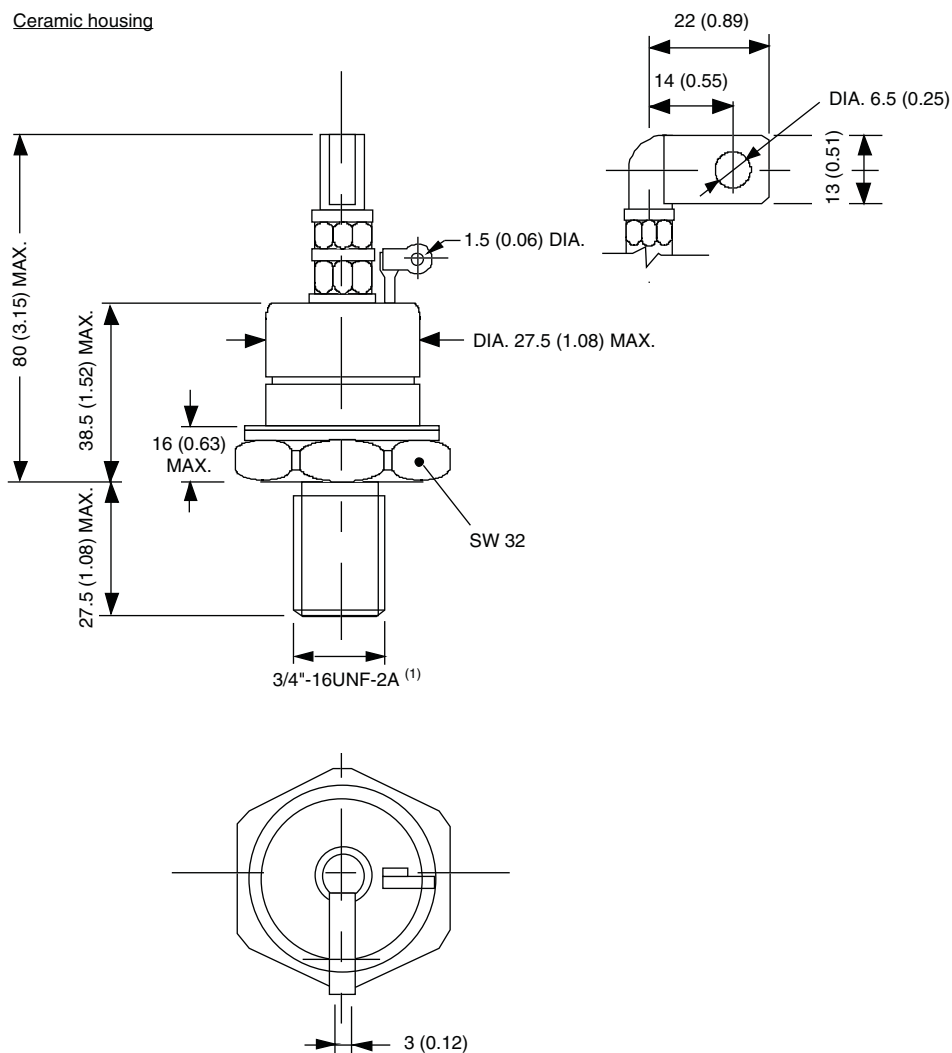
DIMENSIONS - TO-209AB (TO-93) in millimeters (inches)



Note

(1) For metric device: M16 x 1.5 - length 21 (0.83) maximum

DIMENSIONS - TO-209AB (TO-93) FLAG TERMINALS in millimeters (inches)



Note

⁽²⁾ For metric device: M16 x 1.5 - length 21 (0.83) maximum



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